

# ABSTRACT

A method for etching a metal layer on which an oxide-based ARC layer is coated in a semiconductor device comprises the step of performing a dry cleaning process by using a  $\text{Cl}_2/\text{CHF}_3$  based gas, after dry cleaning the ARC layer by using the oxide-based gas. As a result, the etching rates of the center area and the edge area are substantially same.

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